

# PHB18NQ10T

# N-channel TrenchMOS standard level FET Rev. 02 — 17 December 2010

Product data sheet

#### **Product profile** 1.

## 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

#### 1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

## 1.3 Applications

DC-to-DC converters

Switched-mode power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	$T_{mb} = 25  ^{\circ}C;  V_{GS} = 10  V$	-	-	18	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	-	79	W
Static char	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 25 \text{ °C}$	-	80	90	mΩ
Dynamic cl	haracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 18 \text{ A};$ $V_{DS} = 80 \text{ V}; T_j = 25 \text{ °C}$	-	8	-	nC



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain	ng base; connected to	
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make connection to pin 2.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHB18NQ10T	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}$	-	13	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 ^{\circ}\text{C}$	-	18	Α
I <sub>DM</sub>	peak drain current	pulsed; T <sub>mb</sub> = 25 °C	-	72	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	79	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	18	Α
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	72	Α
Avalanche r	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 11 A; $V_{sup} \le$ 25 V; unclamped; $t_p$ = 100 µs; $R_{GS}$ = 50 $\Omega$	-	70	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; unclamped$	-	18	Α

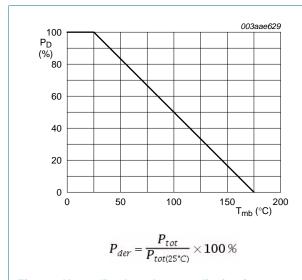


Fig 1. Normalized total power dissipation as a function of mounting base temperature

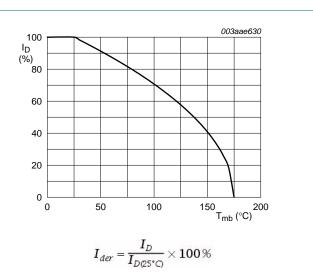


Fig 2. Normalized continuous drain current as a function of mounting base temperature

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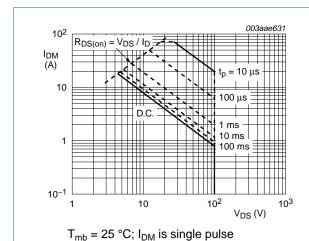


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

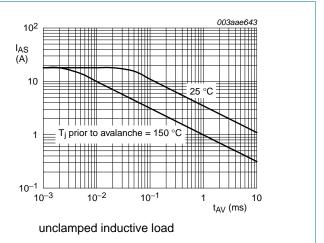


Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.9	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	50	-	K/W

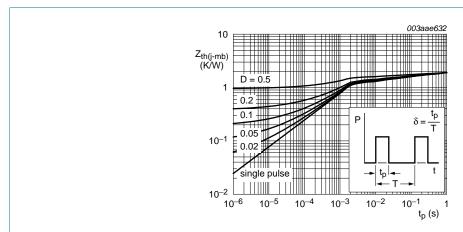


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

# 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub> drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V	
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$ gate-source threshold voltage	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 175 \text{ °C}$	-	-	243	mΩ
resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C	-	80	90	mΩ	
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 18 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	21	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	4	-	nC
$Q_{GD}$	gate-drain charge		-	8	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	633	-	pF
Coss	output capacitance	$T_j = 25 ^{\circ}\text{C}$	-	103	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	61	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2.7 \Omega; V_{GS} = 10 \text{ V};$	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 \text{ °C}$	-	36	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	18	-	ns
t <sub>f</sub>	fall time		-	12	-	ns
L <sub>D</sub>	internal drain inductance	measured from tab to centre of die ; $T_j = 25  ^{\circ}\text{C}$	-	3.5	-	nΗ
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad; $T_j = 25$ °C	-	7.5	-	nΗ
Source-di	rain diode					
$V_{SD}$	source-drain voltage	$I_S = 18 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.92	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 18 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	55	-	ns
Qr	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	135	-	nC

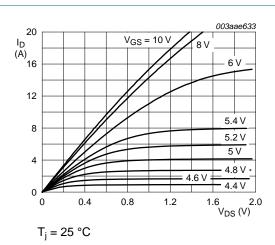


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

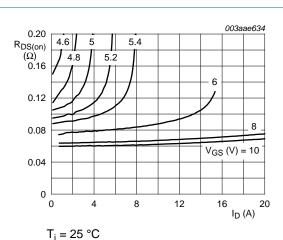


Fig 7. Drain-source on-state resistance as a function of drain current; typical values

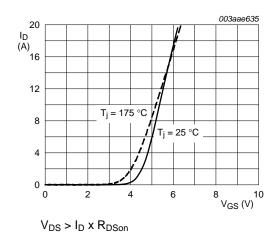


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

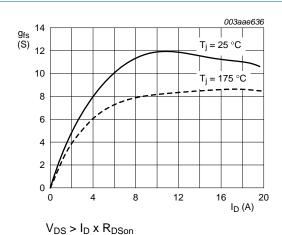


Fig 9. Forward transconductance as a function of drain current; typical values

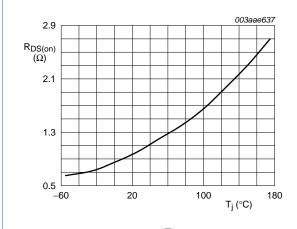


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

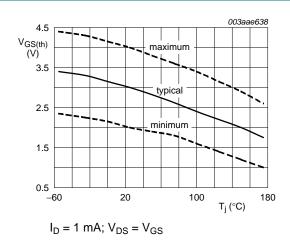


Fig 11. Gate-source threshold voltage as a function of junction temperature

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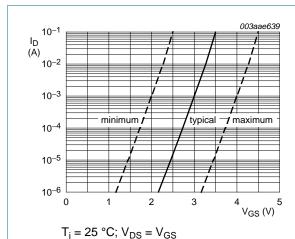
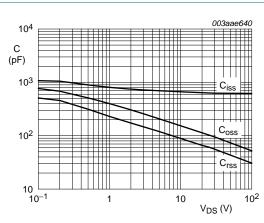
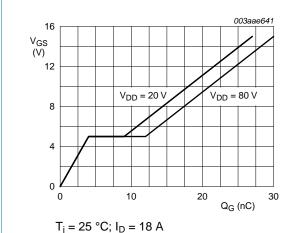


Fig 12. Sub-threshold drain current as a function of gate-source voltage



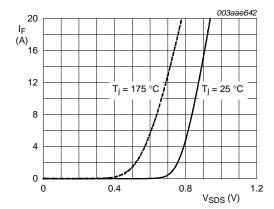
 $V_{GS} = 0 V$ ; f = 1 MHz

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



1<sub>1</sub> = 25 C, 1<sub>D</sub> = 16 A

Fig 14. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$ 

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# 7. Package outline

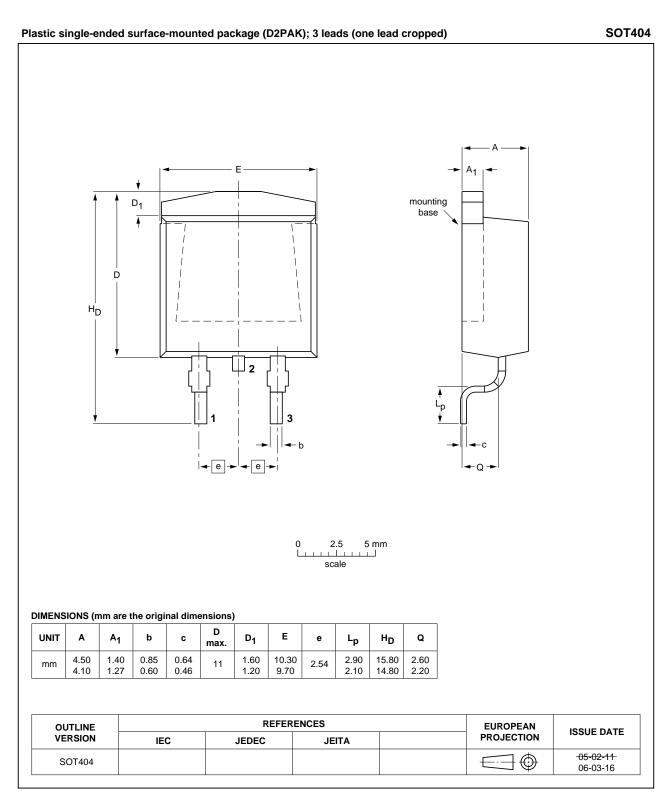


Fig 16. Package outline SOT404 (D2PAK)

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# 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHB18NQ10T v.2	20101217	Product data sheet	-	PHB_PHD_PHP18NQ10T v.1
Modifications:	ations:  • The format of this data sheet has been redesigned to comply with the new iden guidelines of NXP Semiconductors.			omply with the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to the	e new company na	me where appropriate.
	<ul> <li>Type numb</li> </ul>	er PHB18NQ10T separat	ed from data shee	t PHB_PHD_PHP18NQ10T v.1.
PHB_PHD_PHP18NQ10T v.1	19990801	Product specification	-	-

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#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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